Course 7

Wednesday, 2 October 2024 09:41

EE557
Course 7 -...

EE-557
Semiconductor devices I

Optoelectronics devices

Génie Electrique et Electronique
Master Program
Prof. Elison Matioli

Outline of the lecture

- Dynamics of carrier generation
- Optoelectronics devices

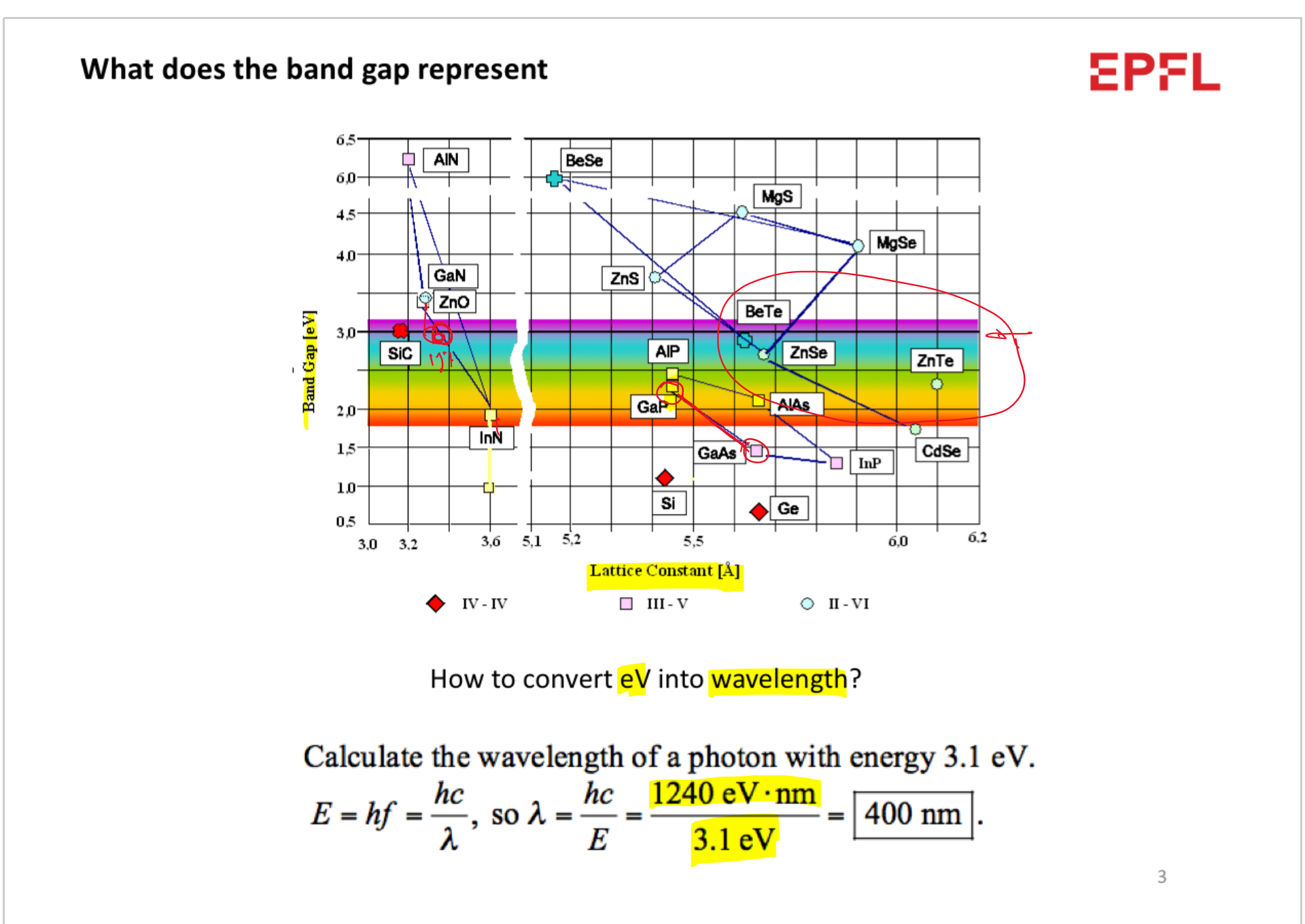
References:

- J. A. del Alamo, course materials for 6.720J Integrated Microelectronic Devices, Spring 2007. MIT OpenCourseWare (http://ocw.mit.edu/)

Carrier Generation and Recombination

Key questions

How are these principles applied to optoelectronic devices?

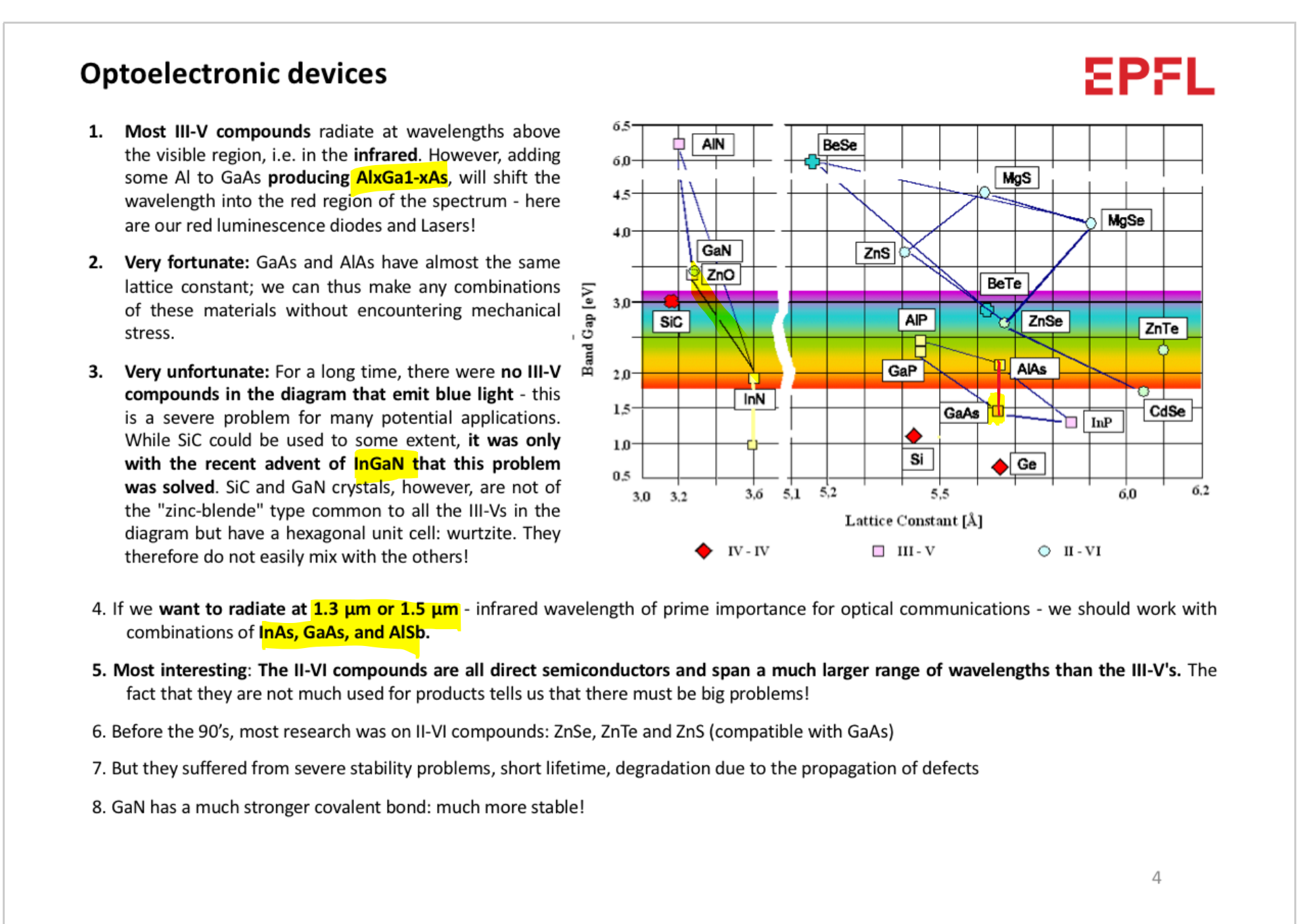


What does the band gap represent

How to convert eV into wavelength?

Calculate the wavelength of a photon with energy 3.1 eV.

$$E = hf = \frac{hc}{\lambda},\ \text{so}\ \lambda = \frac{hc}{E} = \frac{1240\ \text{eV}\cdot\text{nm}}{3.1\ \text{eV}} = \boxed{400\ \text{nm}}.$$

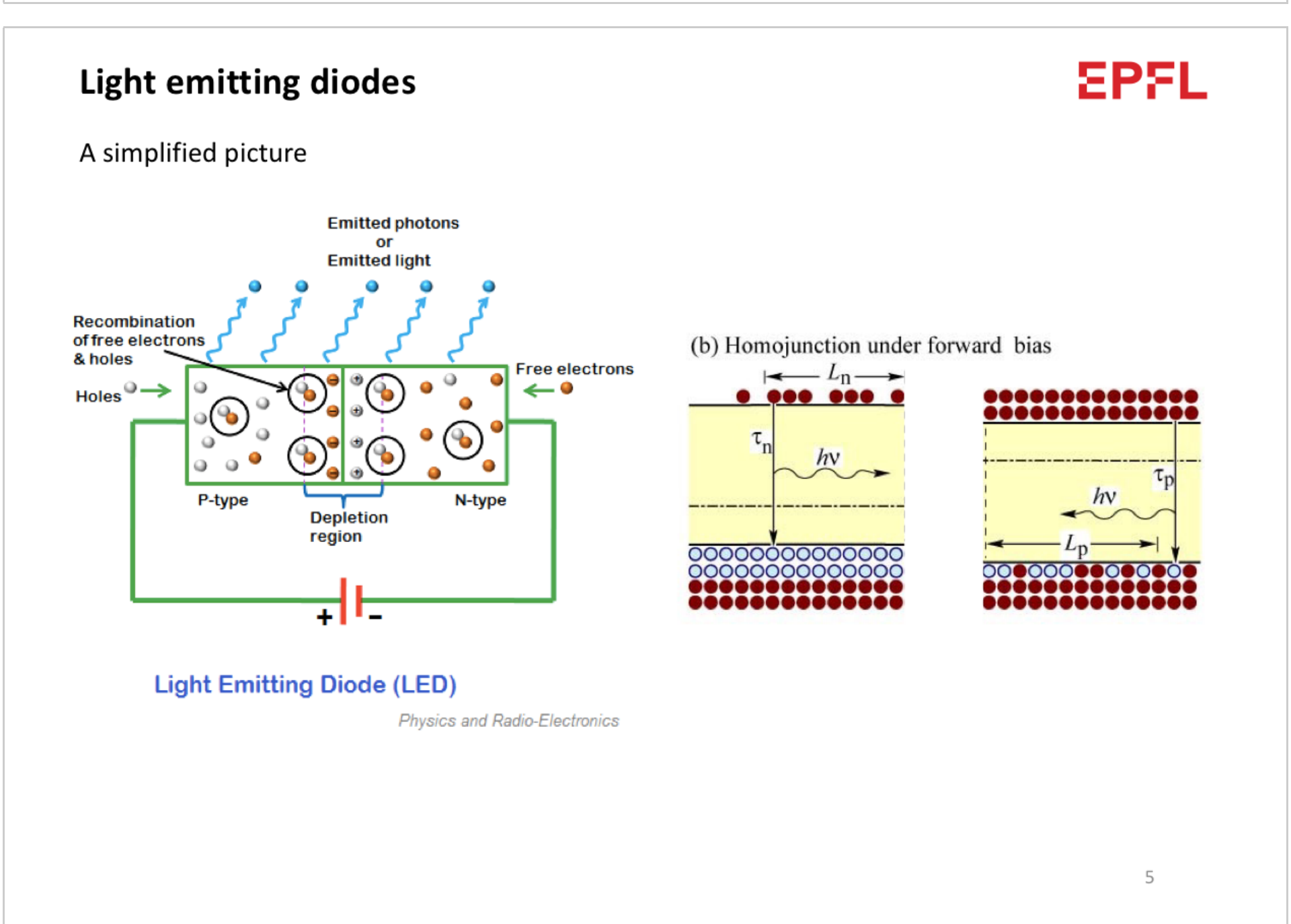


Optoelectronic devices

1. **Most III-V compounds** radiate at wavelengths above the visible region, i.e. in the **infrared**. However, adding some Al to GaAs **producing AlxGa1-xAs**, will shift the wavelength into the red region of the spectrum - here are our red luminescence diodes and Lasers!
2. **Very fortunate:** GaAs and AlAs have almost the same lattice constant; we can thus make any combinations of these materials without encountering mechanical stress.
3. **Very unfortunate:** For a long time, there were **no III-V compounds in the diagram that emit blue light** - this is a severe problem for many potential applications. While SiC could be used to some extent, **it was only with the recent advent of InGaN that this problem was solved**. SiC and GaN crystals, however, are not of the "zinc-blende" type common to all the III-Vs in the diagram but have a hexagonal unit cell: wurtzite. They therefore do not easily mix with the others!

Band Gap [eV]
Lattice Constant [Å]
IV - IV
III - V
II - VI

4. If we **want to radiate at 1.3 µm or 1.5 µm** - infrared wavelength of prime importance for optical communications - we should work with combinations of **InAs, GaAs, and AlSb**.
5. **Most interesting: The II-VI compounds are all direct semiconductors and span a much larger range of wavelengths than the III-V's.** The fact that they are not much used for products tells us that there must be big problems!
6. Before the 90's, most research was on II-VI compounds: ZnSe, ZnTe and ZnS (compatible with GaAs)
7. But they suffered from severe stability problems, short lifetime, degradation due to the propagation of defects
8. GaN has a much stronger covalent bond: much more stable!



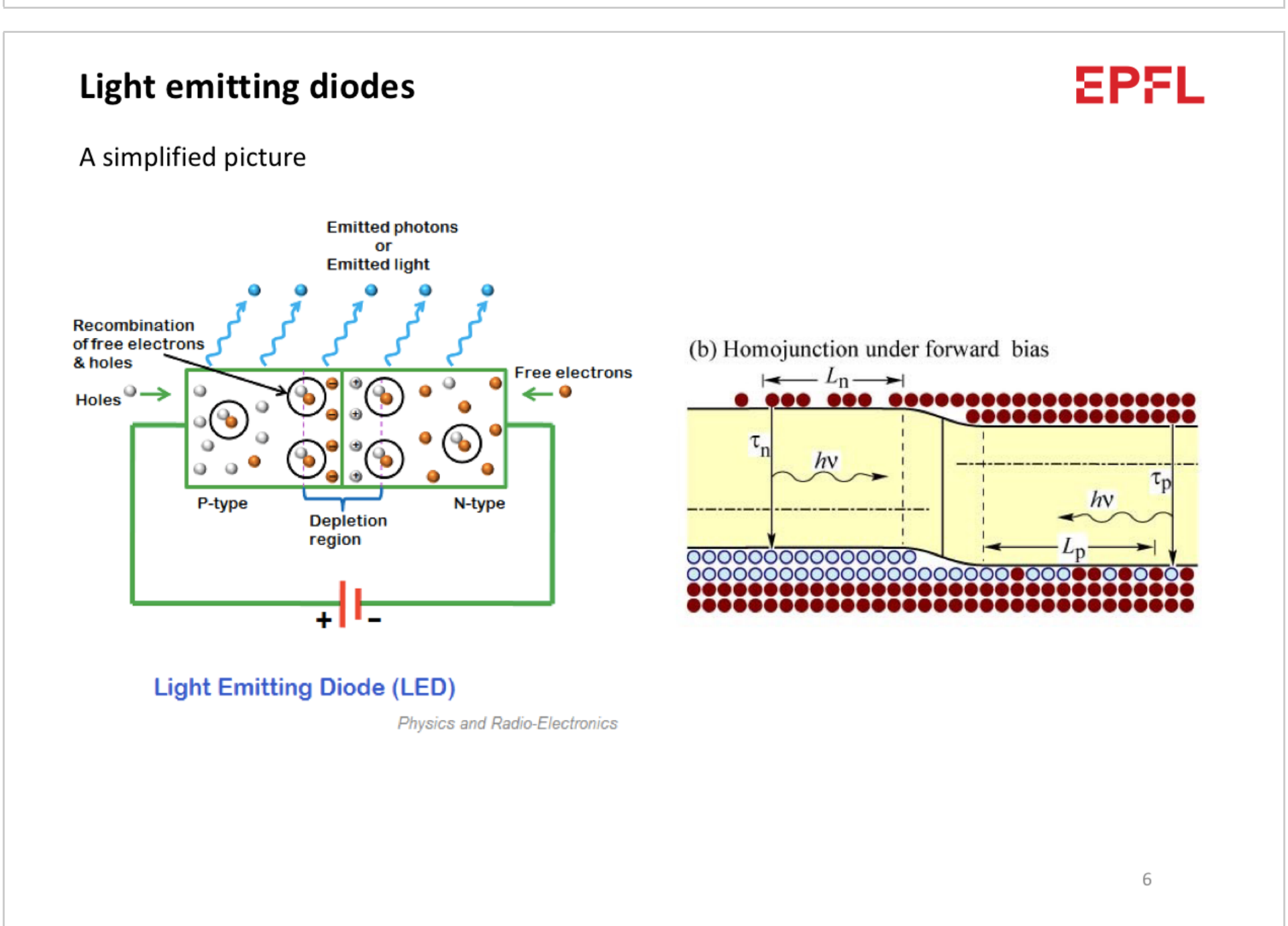
Light emitting diodes

A simplified picture

Emitted photons
or
Emitted light
Recombination of free electrons & holes
Holes
Free electrons
P-type
Depletion region
N-type
(b) Homojunction under forward bias
L_n
τ_n
$h\nu$
τ_p
L_p

Light Emitting Diode (LED)

Physics and Radio-Electronics



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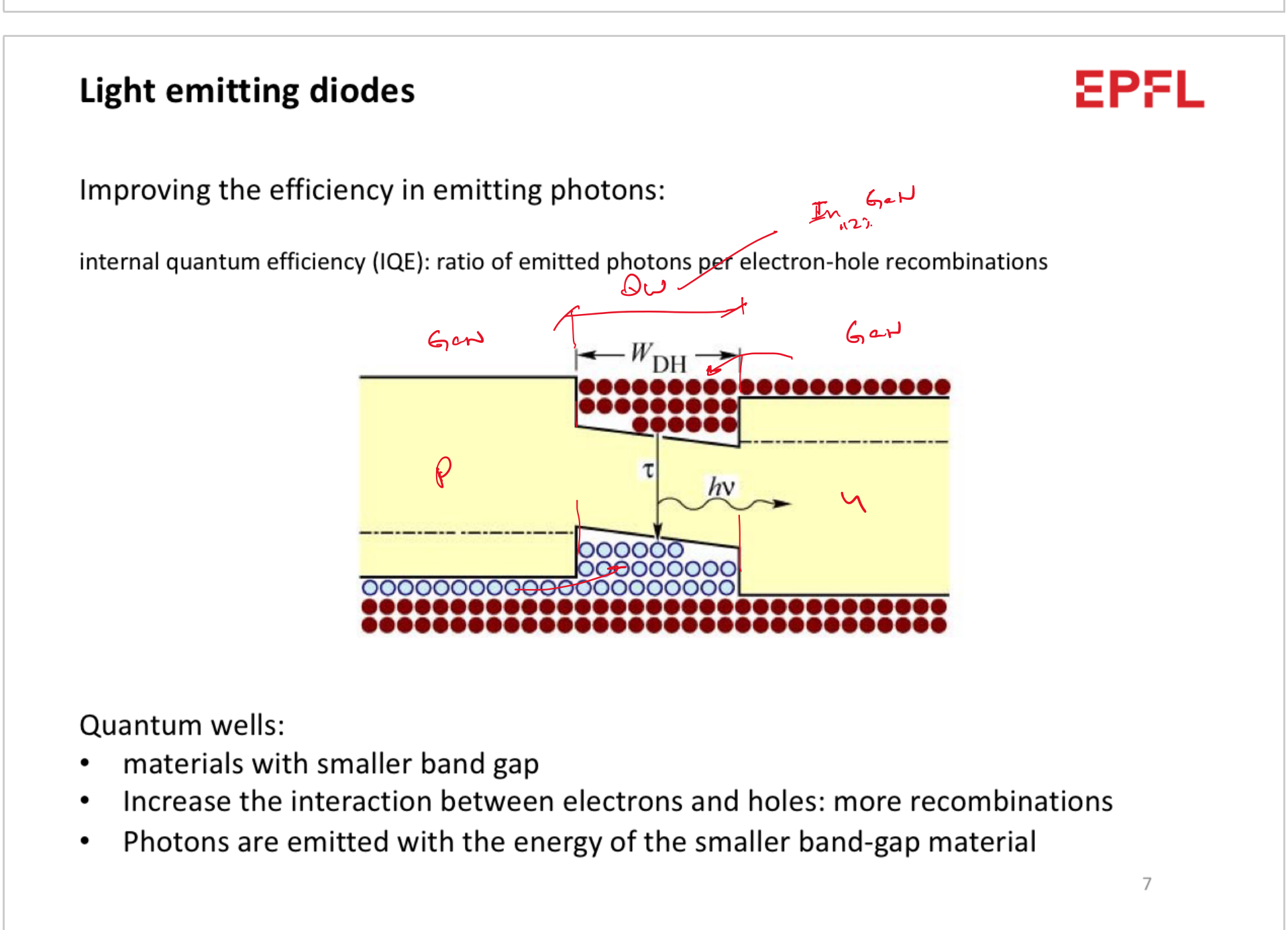
Light Emitting Diode (LED)

Physics and Radio-Electronics



Light emitting diodes

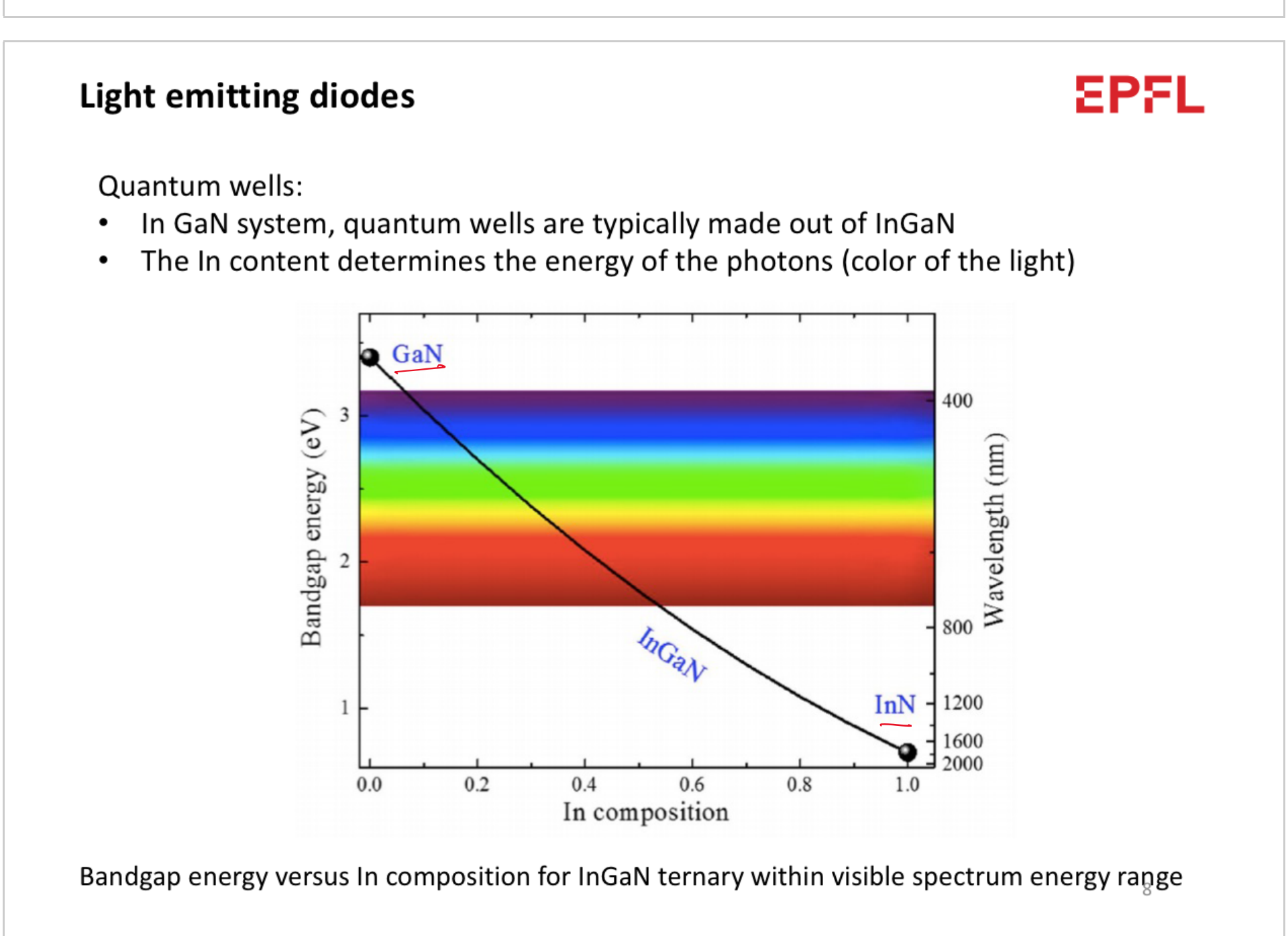
Improving the efficiency in emitting photons:

internal quantum efficiency (IQE): ratio of emitted photons per electron-hole recombinations

In GaN
QW
GaN
GaN
W_{DH}
p
τ
$h\nu$
n

Quantum wells:

- materials with smaller band gap
- Increase the interaction between electrons and holes: more recombinations
- Photons are emitted with the energy of the smaller band-gap material

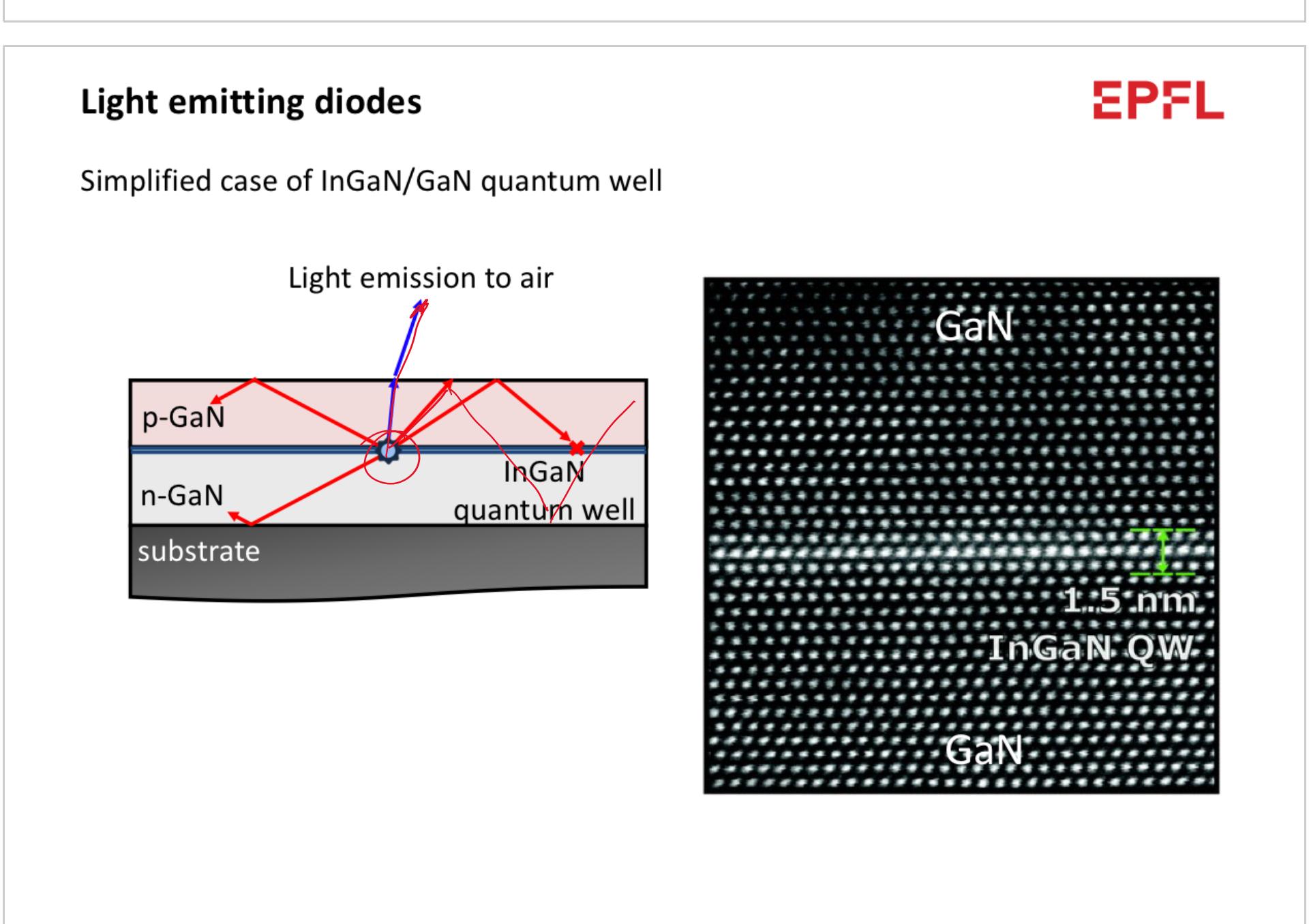


Light emitting diodes

Quantum wells:

- In GaN system, quantum wells are typically made out of InGaN
- The In content determines the energy of the photons (color of the light)

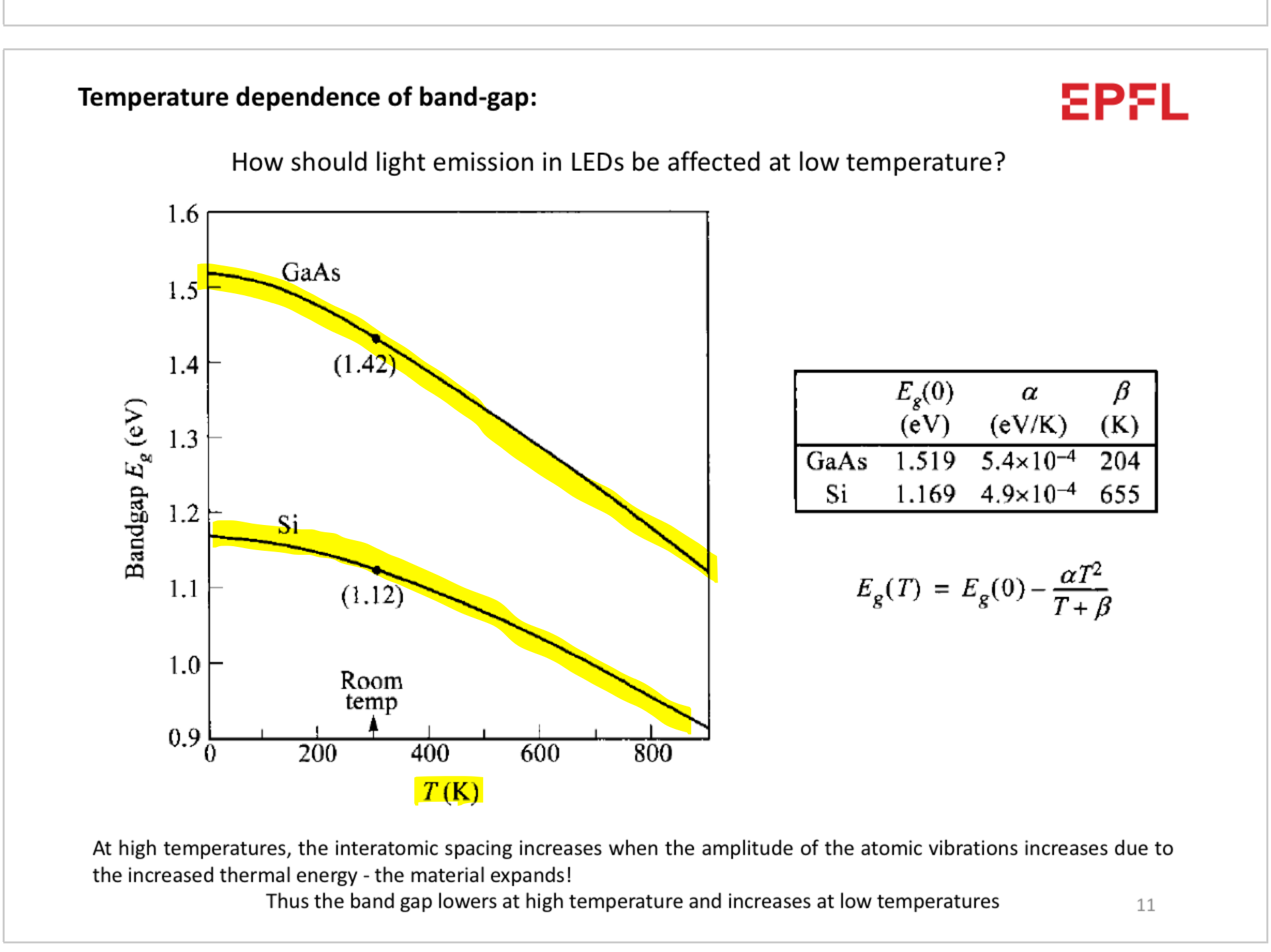
Bandgap energy versus In composition for InGaN ternary within visible spectrum energy range



Light emitting diodes

Simplified case of InGaN/GaN quantum well

Light emission to air
p-GaN
n-GaN
InGaN quantum well
substrate
GaN
1.5 nm
InGaN QW
GaN



Temperature dependence of band-gap:

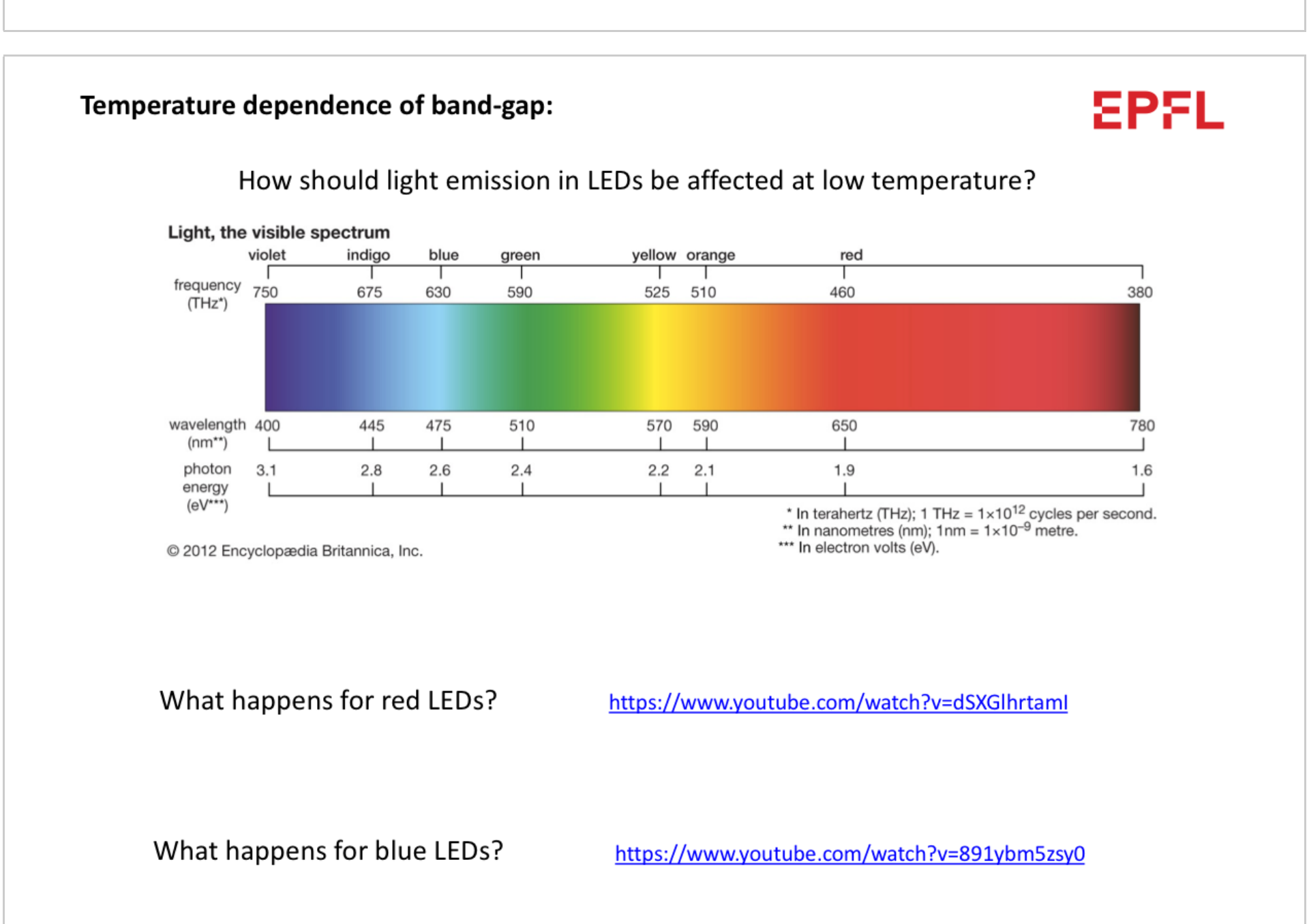
How should light emission in LEDs be affected at low temperature?

	$E_g(0)$ (eV)	α (eV/K)	β (K)
GaAs	1.519	5.4×10^{-4}	204
Si	1.169	4.9×10^{-4}	655

$$E_g(T) = E_g(0) - \frac{\alpha T^2}{T+\beta}$$

At high temperatures, the interatomic spacing increases when the amplitude of the atomic vibrations increases due to the increased thermal energy - the material expands!

Thus the band gap lowers at high temperature and increases at low temperatures



Temperature dependence of band-gap:

How should light emission in LEDs be affected at low temperature?

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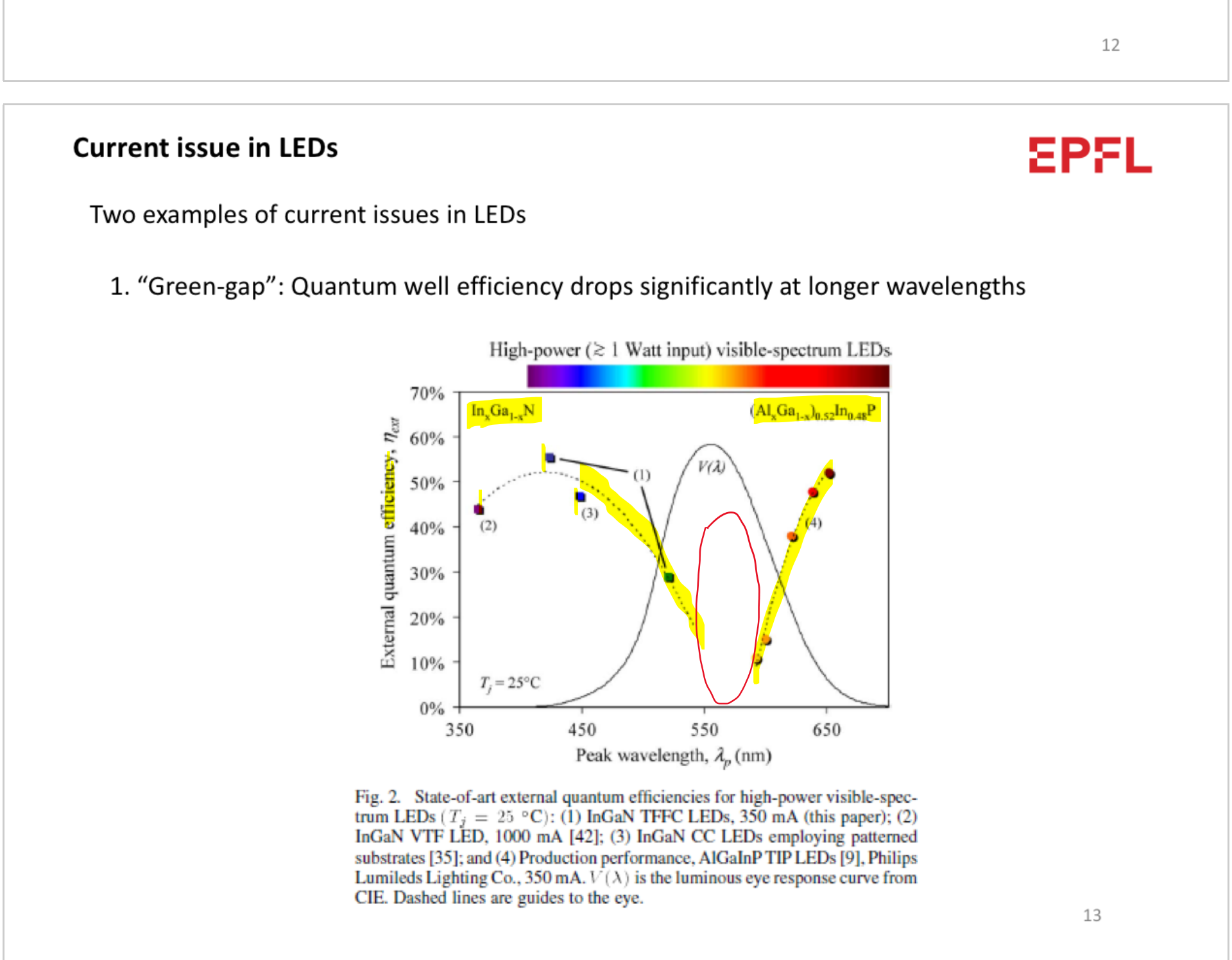
What happens for red LEDs? https://www.youtube.com/watch?v=dSXGlhrtamI

What happens for blue LEDs? https://www.youtube.com/watch?v=891ybm5zsy0

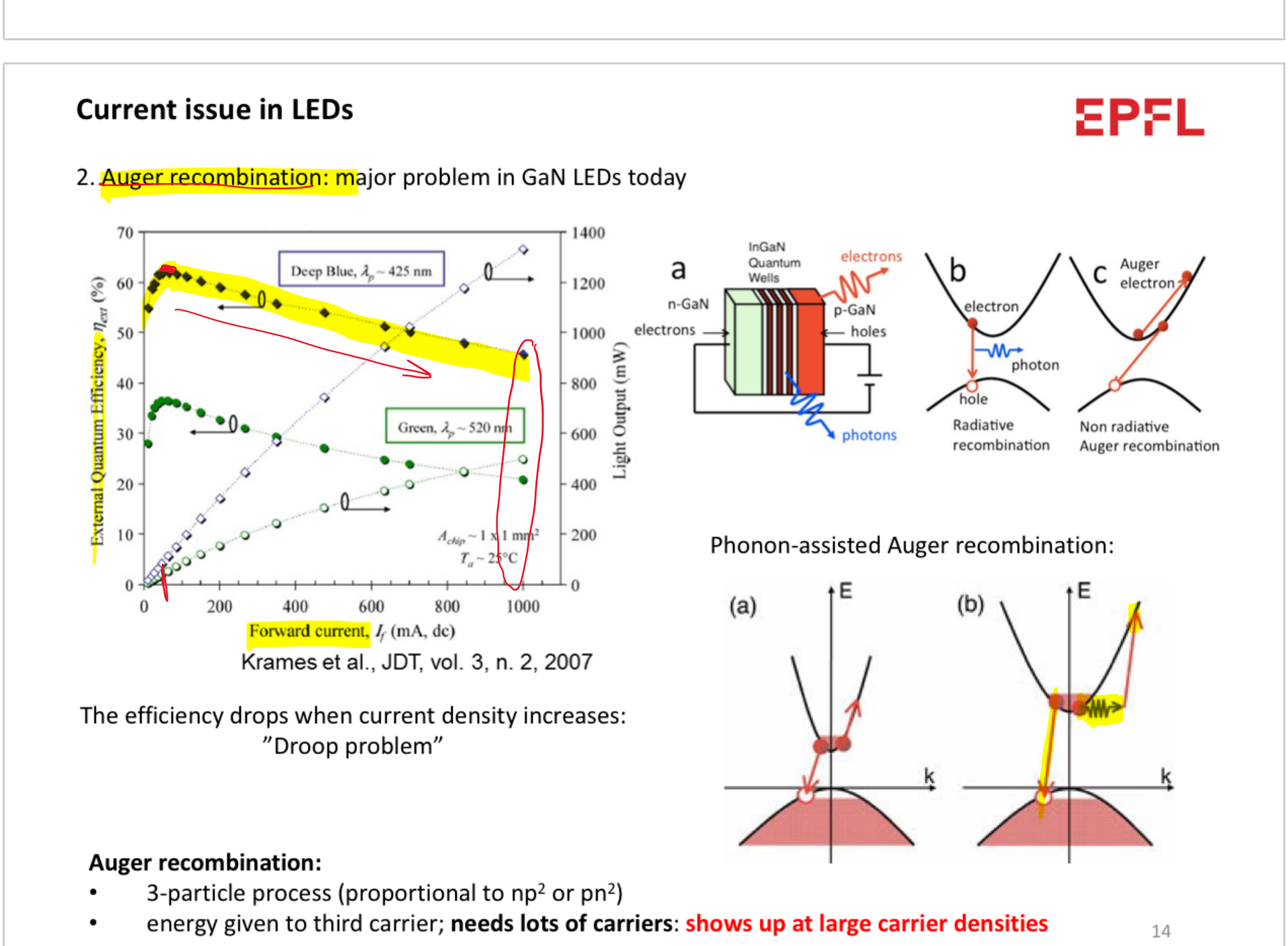


Current issue in LEDs

Two examples of current issues in LEDs

1. "Green-gap": Quantum well efficiency drops significantly at longer wavelengths

Fig. 2. State-of-art external quantum efficiencies for high-power visible-spectrum LEDs (T_j = 25 °C): (1) InGaN TFFC LEDs, 350 mA (this paper); (2) InGaN VTF LED, 1000 mA [42]; (3) InGaN CC LEDs employing patterned substrates [35]; and (4) Production performance, AlGaInP TIP LEDs [9], Philips Lumileds Lighting Co., 350 mA. $V(\lambda)$ is the luminous eye response curve from CIE. Dashed lines are guides to the eye.



Current issue in LEDs

2. Auger recombination: major problem in GaN LEDs today

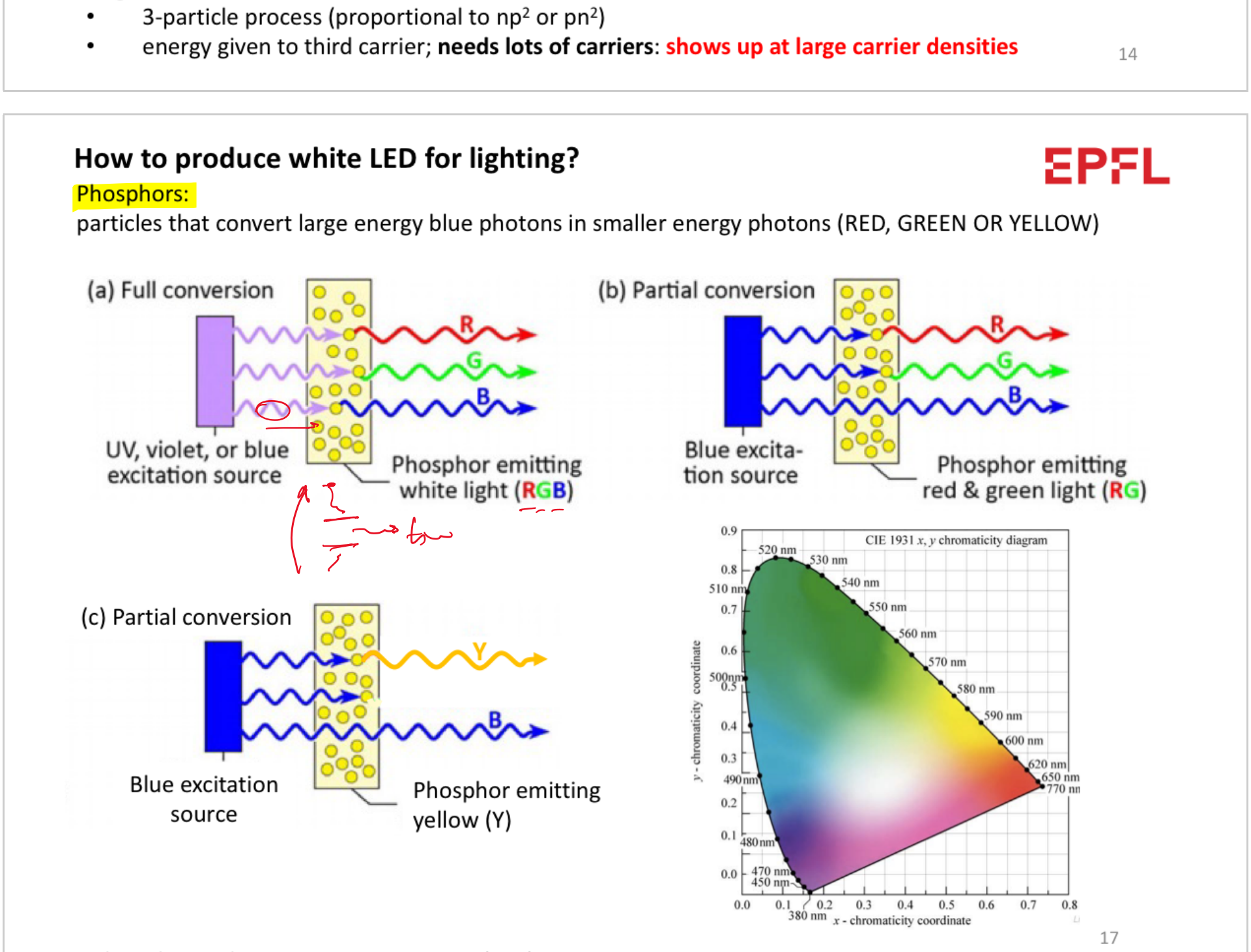
Krames et al., JDT, vol. 3, n. 2, 2007

The efficiency drops when current density increases:
"Droop problem"

Phonon-assisted Auger recombination:

Auger recombination:

- 3-particle process (proportional to np^2 or pn^2)
- energy given to third carrier; **needs lots of carriers**: **shows up at large carrier densities**



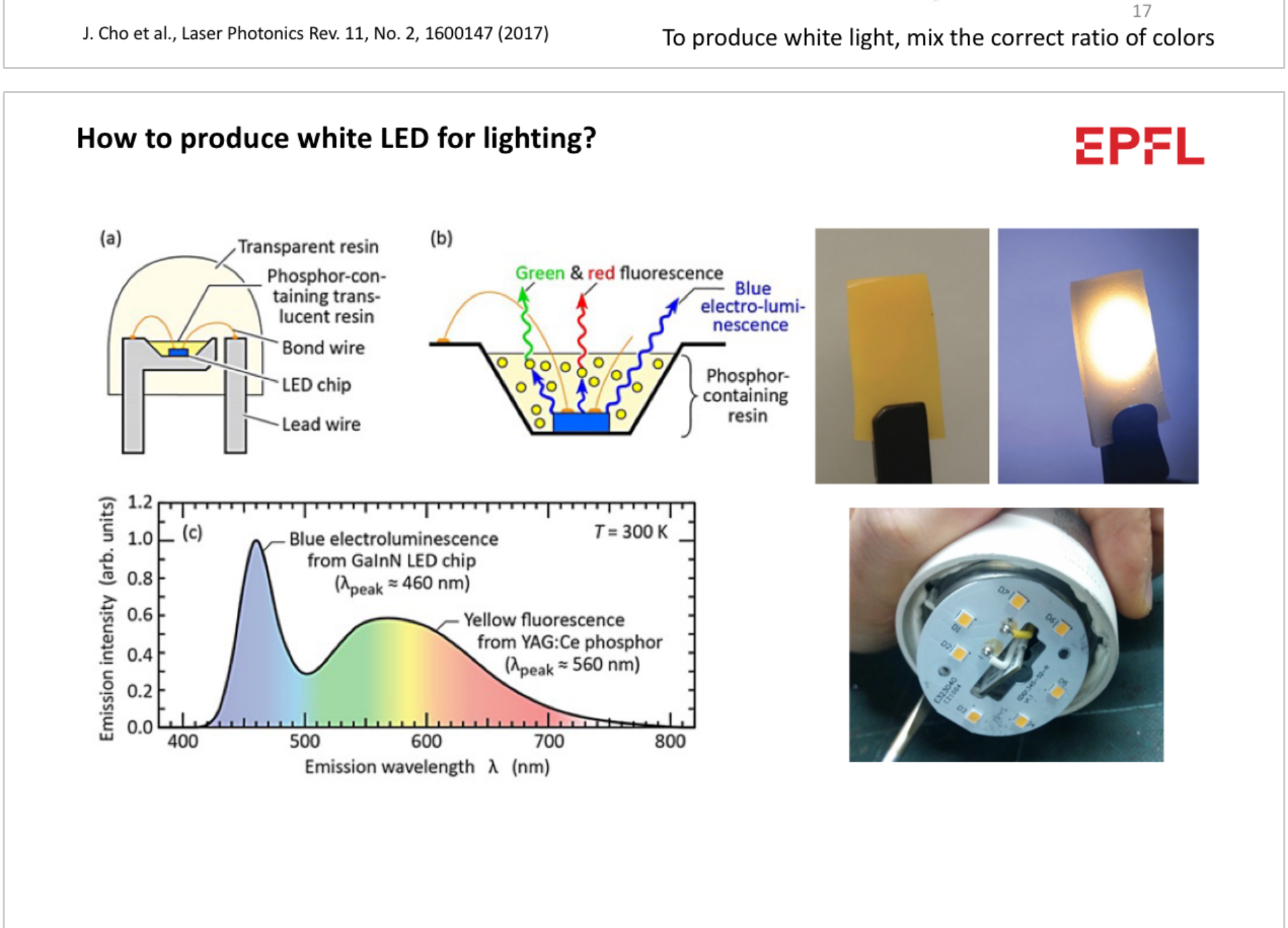
How to produce white LED for lighting?

Phosphors:
particles that convert large energy blue photons in smaller energy photons (RED, GREEN OR YELLOW)

(a) Full conversion
UV, violet, or blue excitation source
Phosphor emitting white light (RGB)
(b) Partial conversion
Blue excitation source
Phosphor emitting red & green light (RG)
(c) Partial conversion
Blue excitation source
Phosphor emitting yellow (Y)
R
G
B
Y
CIE 1931 x, y chromaticity diagram
x - chromaticity coordinate
y - chromaticity coordinate

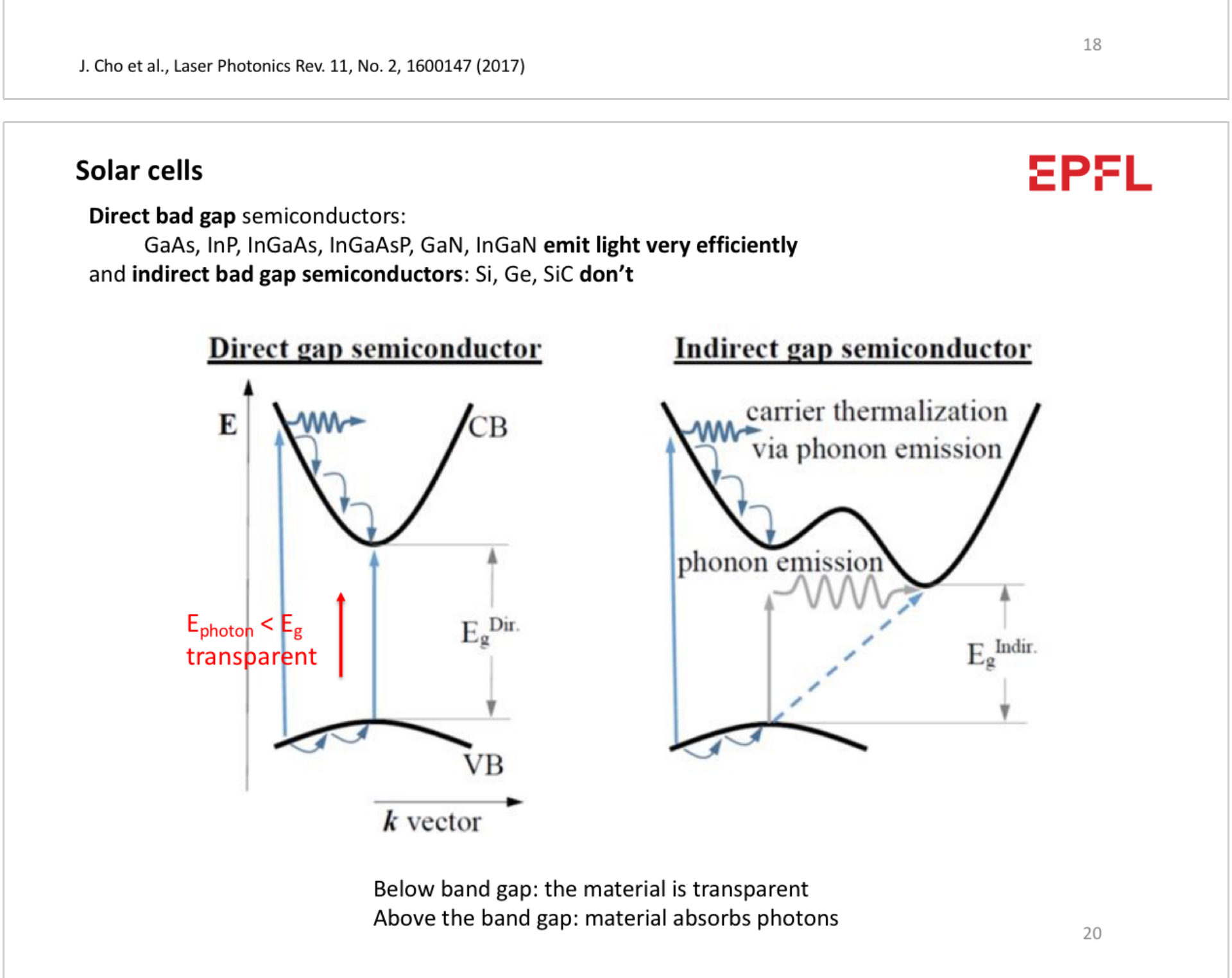
J. Cho et al., Laser Photonics Rev. 11, No. 2, 1600147 (2017)

To produce white light, mix the correct ratio of colors



How to produce white LED for lighting?

J. Cho et al., Laser Photonics Rev. 11, No. 2, 1600147 (2017)

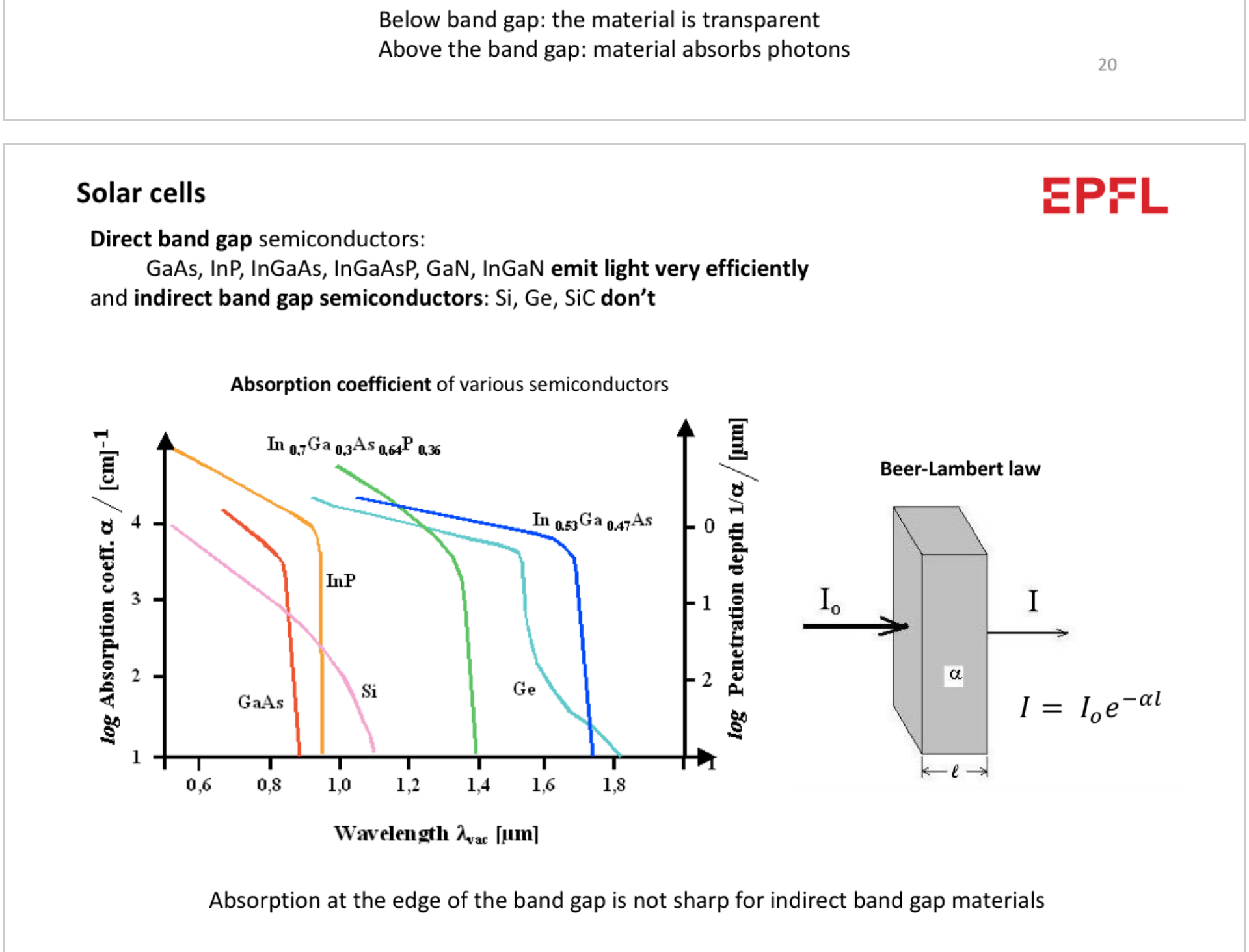


Solar cells

Direct bad gap semiconductors:
GaAs, InP, InGaAs, InGaAsP, GaN, InGaN **emit light very efficiently**
and **indirect bad gap semiconductors**: Si, Ge, SiC **don't**

Direct gap semiconductor
E
CB
$E_{photon} < E_g$
transparent
$E_g^{Dir.}$
VB
k vector
Indirect gap semiconductor
carrier thermalization via phonon emission
phonon emission
$E_g^{Indir.}$

Below band gap: the material is transparent
Above the band gap: material absorbs photons



Solar cells

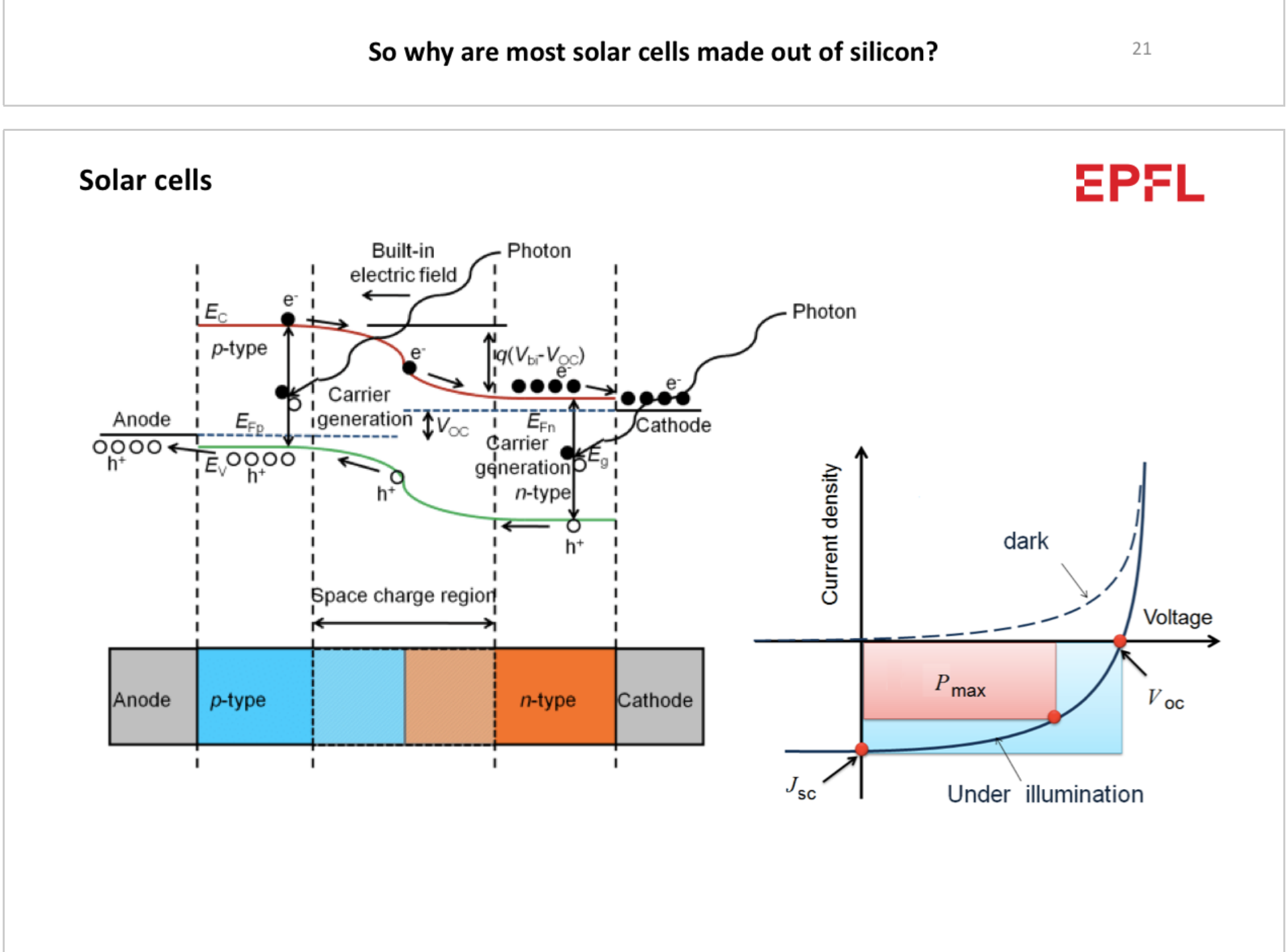
Direct band gap semiconductors:
GaAs, InP, InGaAs, InGaAsP, GaN, InGaN **emit light very efficiently**
and **indirect band gap semiconductors**: Si, Ge, SiC **don't**

Absorption coefficient of various semiconductors

$$I = I_o e^{-\alpha l}$$

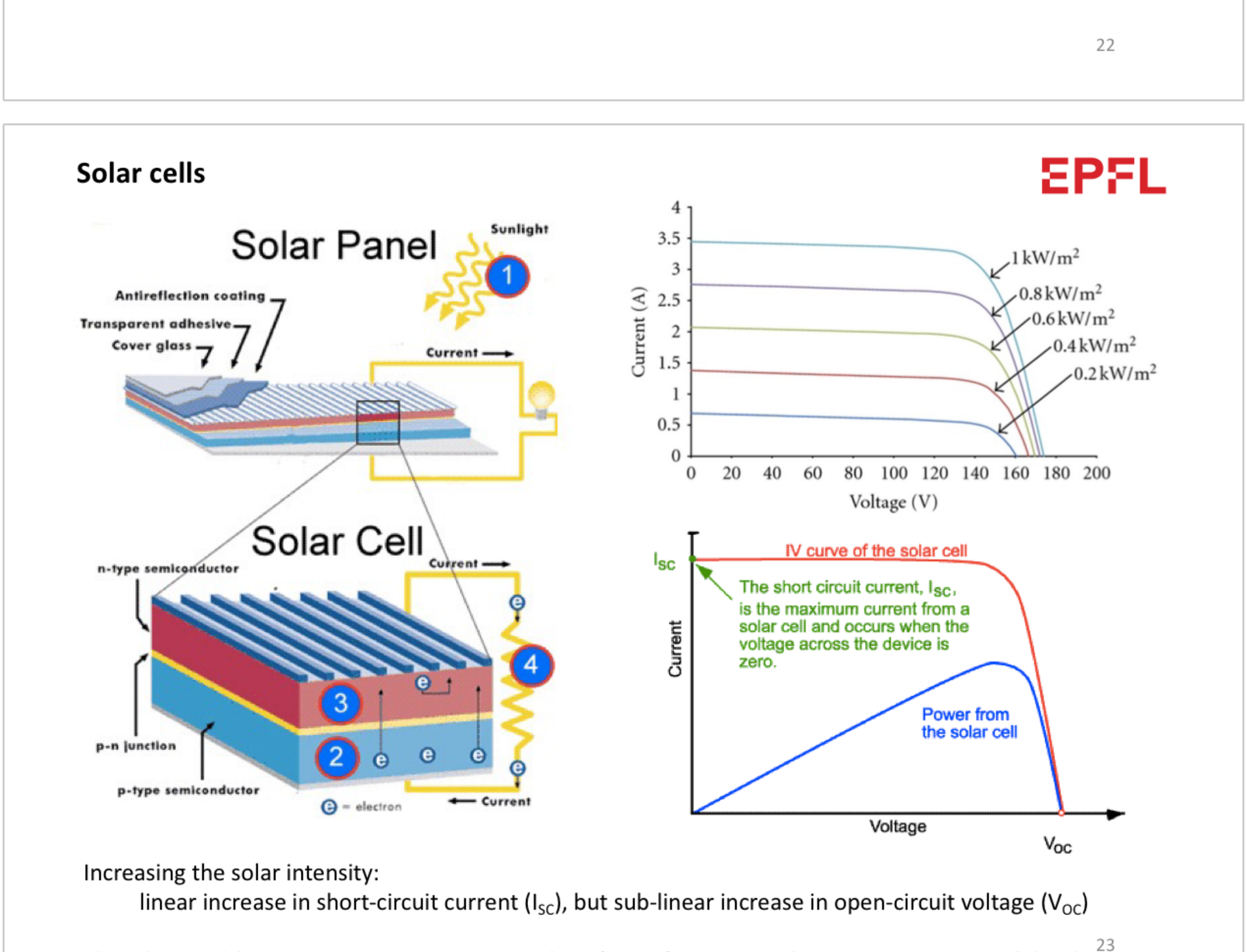
Absorption at the edge of the band gap is not sharp for indirect band gap materials

So why are most solar cells made out of silicon?



Solar cells

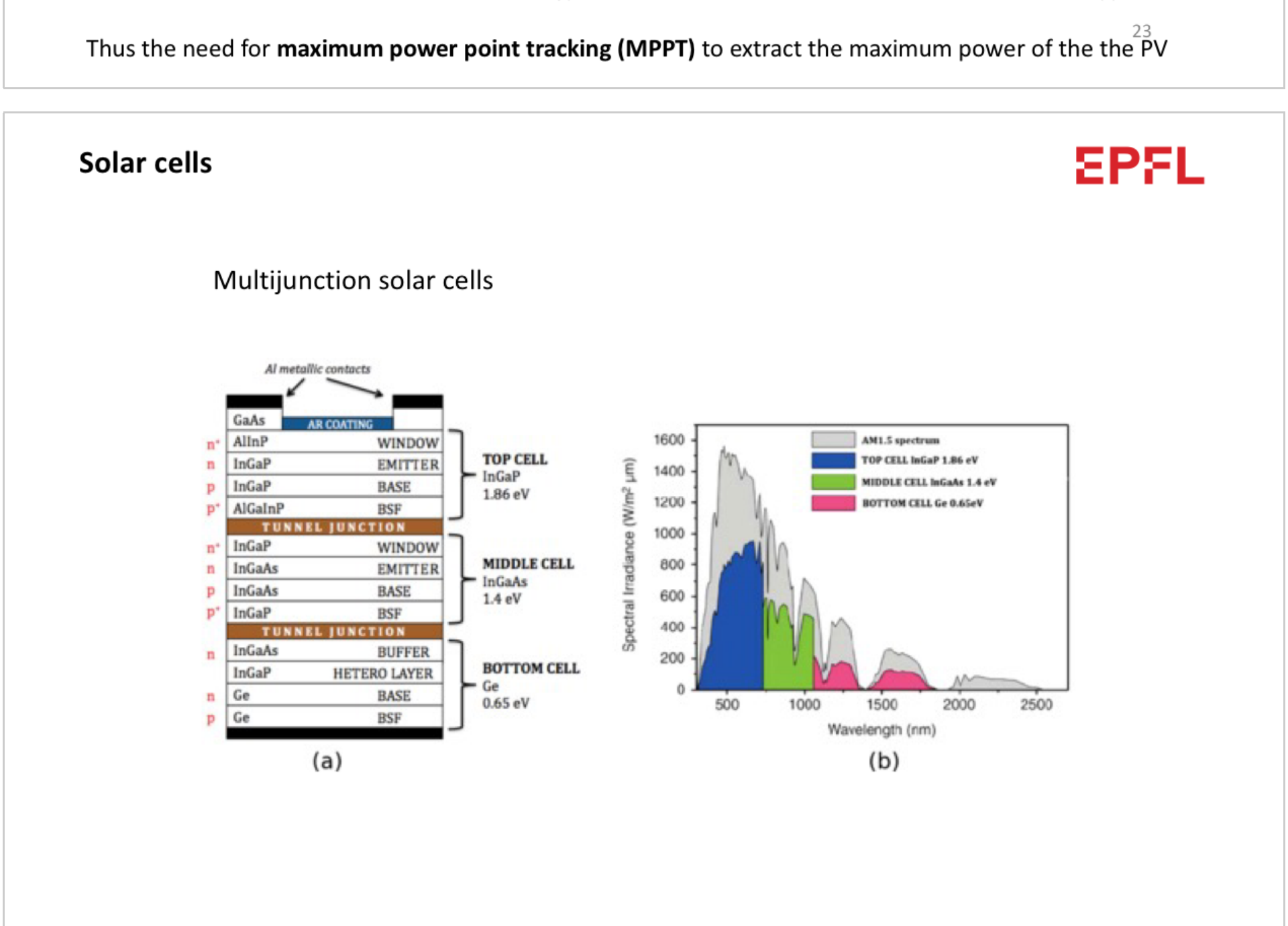
Built-in electric field
Photon
E_C
p-type
Carrier generation
$q(V_{bi}-V_{OC})$
V_{OC}
E_{Fp}
E_{Fn}
E_V
Anode
Cathode
Carrier generation
n-type
E_g
Space charge region
Anode
p-type
n-type
Cathode
Current density
dark
Voltage
P_{max}
V_{oc}
J_{sc}
Under illumination



Solar cells

Increasing the solar intensity:
linear increase in short-circuit current (I_{SC}), but sub-linear increase in open-circuit voltage (V_{OC})

Thus the need for **maximum power point tracking (MPPT)** to extract the maximum power of the the PV

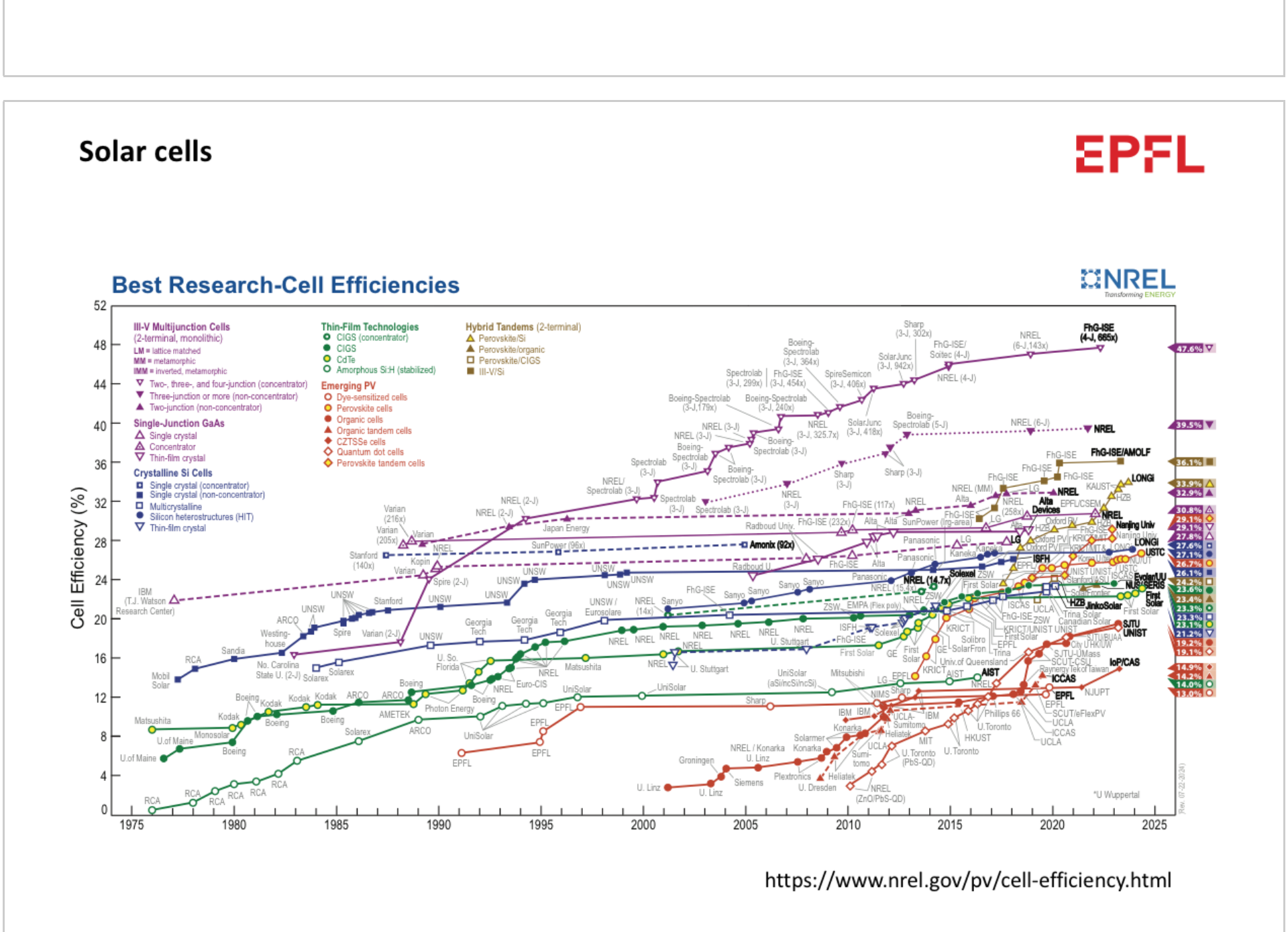


Solar cells

Multijunction solar cells

Al metallic contacts
GaAs
AR COATING
AlInP WINDOW
InGaP EMITTER
InGaP BASE
AlGaInP BSF
TUNNEL JUNCTION
InGaP WINDOW
InGaAs EMITTER
InGaAs BASE
InGaP BSF
TUNNEL JUNCTION
InGaAs BUFFER
InGaP HETERO LAYER
Ge BASE
Ge BSF
TOP CELL InGaP 1.86 eV
MIDDLE CELL InGaAs 1.4 eV
BOTTOM CELL Ge 0.65 eV
AM1.5 spectrum
TOP CELL InGaP 1.86 eV
MIDDLE CELL InGaAs 1.4 eV
BOTTOM CELL Ge 0.65eV
Spectral Irradiance (W/m² µm)
Wavelength (nm)

(a) (b)



Solar cells

https://www.nrel.gov/pv/cell-efficiency.html